

# Devanarayanan Ettisserry

## List of Publications by Year in descending order

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9  
papers

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1684188  
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docs citations

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times ranked

132  
citing authors

#	ARTICLE	IF	CITATIONS
1	Role of Oxygen Vacancies in Short- and Long-Term Instability of Negative Bias-Temperature Stressed SiC MOSFETs. IEEE Transactions on Electron Devices, 2017, 64, 1007-1014.	3.0	11
2	Negative bias-and-temperature stress-assisted activation of oxygen-vacancy hole traps in 4H-silicon carbide metal-oxide-semiconductor field-effect transistors. Journal of Applied Physics, 2015, 118, .	2.5	13
3	Modeling of oxygen-vacancy hole trap activation in 4H-SiC MOSFETs using density functional theory and rate equation analysis. , 2015, , .		2
4	Using density functional theory to engineer direct gap germanium-tin alloy. , 2015, , .		2
5	Structure, bonding, and passivation of single carbon-related oxide hole traps near 4H-SiC/SiO <sub>2</sub> interfaces. Journal of Applied Physics, 2014, 116, .	2.5	26
6	A methodology to identify and quantify mobility-reducing defects in 4H-silicon carbide power metal-oxide-semiconductor field-effect transistors. Journal of Applied Physics, 2014, 115, 103706.	2.5	12
7	Identification and quantification of 4H-SiC (0001)/SiO <sub>2</sub> interface defects by combining density functional and device simulations. , 2013, , .		0
8	Density functional and Monte Carlo-based electron transport simulation in 4H-SiC(0001)/SiO <sub>2</sub> DMOSFET transition region. , 2013, , .		1
9	The effect of defects and their passivation on the density of states of the 4H-silicon-carbide/silicon-dioxide interface. Journal of Applied Physics, 2013, 113, 053703.	2.5	22